

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60V	4.8mΩ@10V	90A
	7.2mΩ@4.5V	

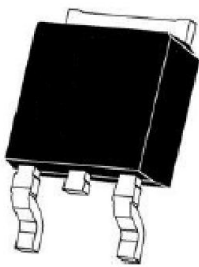
Feature

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Suffix “-Q1” for AEC-Q101

Application

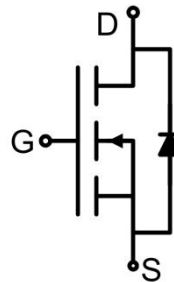
- Power switching application
- DC-DC convertor
- Uninterruptible power supply

Package



TO-252AB

Circuit diagram



Marking



Absolute maximum ratings (T_A=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current (T _C =25°C)	I _D	90	A
Continuous Drain Current (T _C =100°C)	I _D (100°C)	63	A
Pulsed Drain Current Tested ¹⁾	I _{DM}	360	A
Single Pulse Avalanche Energy ²⁾	E _{AS}	144	mJ
Power Dissipation ³⁾ (T _C =25°C)	P _D	115	W
Thermal Resistance Junction to Case	R _{θJC}	1.3	°C/W
Operating Junction Temperature	T _J	-55 ~ +175	°C
Storage Temperature Range	T _{STG}	-55 ~ +175	°C

Electrical characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1	1.6	2.5	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 45A		3.7	4.8	mΩ
		V _{GS} = 4.5V, I _D = 20A		5.5	7.2	
Dynamic characteristics⁴⁾						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		1730		pF
Output Capacitance	C _{oss}			500		
Reverse Transfer Capacitance	C _{rss}			20		
Total Gate Charge	Q _g	V _{DS} = 30V, V _{GS} = 10V, I _D = 45A		34		nC
Gate-Source Charge	Q _{gs}			10		
Gate-Drain Charge	Q _{gd}			9		
Turn-on delay time	t _{d(on)}	V _{DS} = 30V, V _{GS} = 10V, I _D = 45A R _G = 3Ω		15		nS
Turn-on rise time	t _r			56		
Turn-off delay time	t _{d(off)}			30		
Turn-off fall time	t _f			25		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				90	A
Diode Forward voltage	V _{SD}	V _{GS} = 0V, I _S = 45A			1.2	V
Reverse recover time	T _{rr}	I _S = 45A, di/dt = -100A/us		39		nS
Reverse recovery charge	Q _{rr}			45		nC

Notes:

- 1) Repetitive rating; pulse width limited by max. junction temperature.
- 2) T_J=25°C, V_{DD}=40V, V_G=10V, R_G=25Ω, L=1mH, I_{AS}=17A.
- 3) P_D is based on max. junction temperature, using junction-case thermal resistance.
- 4) Guaranteed by design, not subject to production testing.

Typical Characteristics

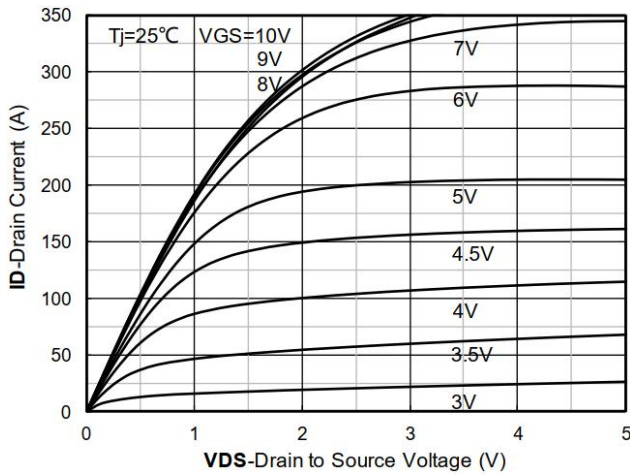


Figure 1. Output Characteristics

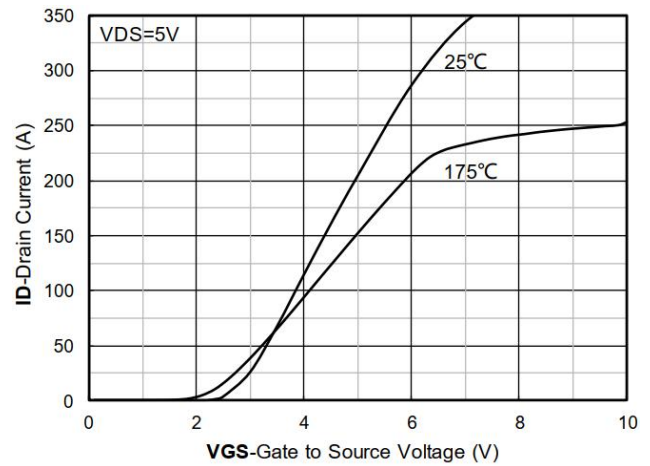


Figure 2. Transfer Characteristics

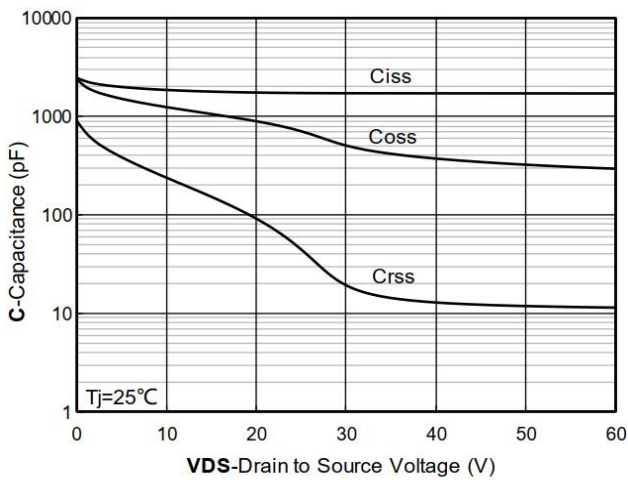


Figure 3. Capacitance Characteristics

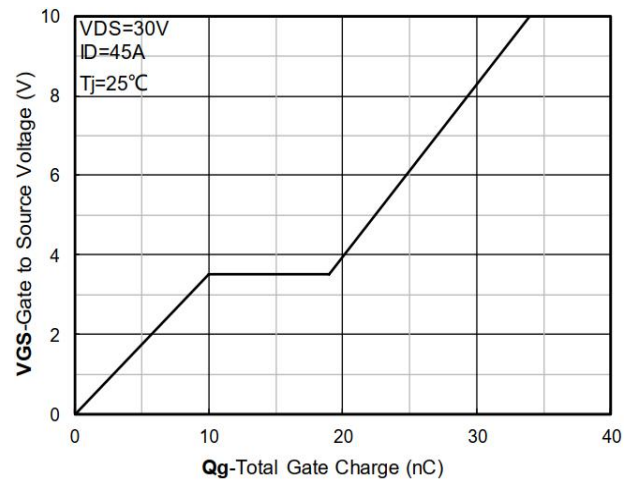


Figure 4. Gate Charge

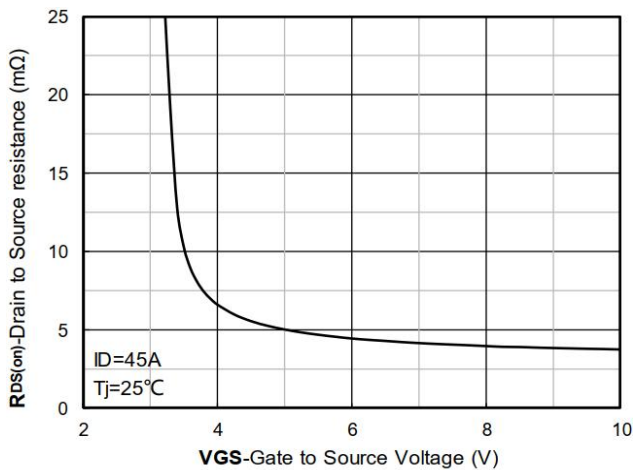


Figure 5. On-Resistance vs Gate to Source Voltage

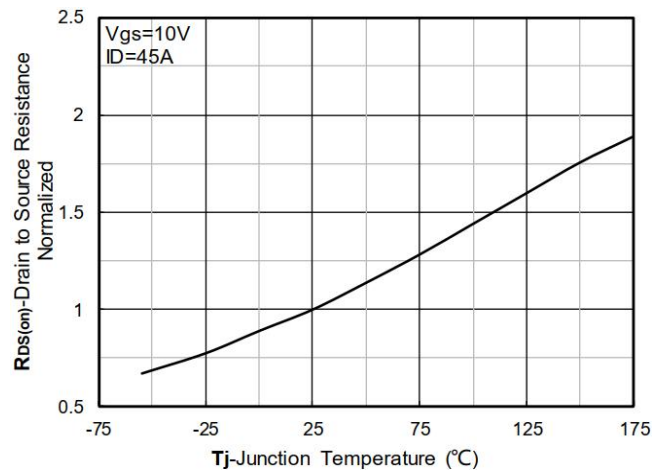


Figure 6. Normalized On-Resistance

Typical Characteristics

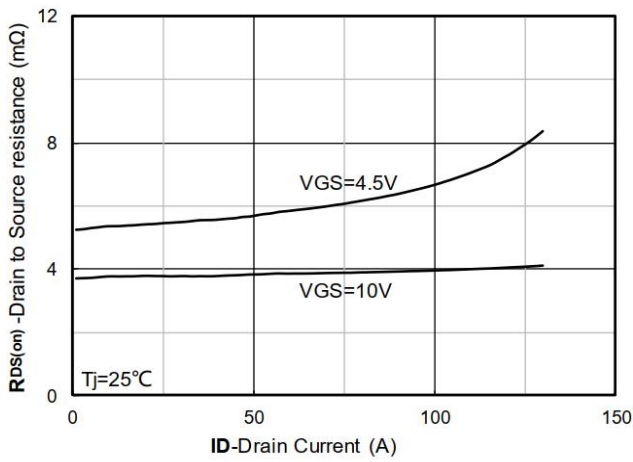


Figure 7. $R_{DS(on)}$ VS Drain Current

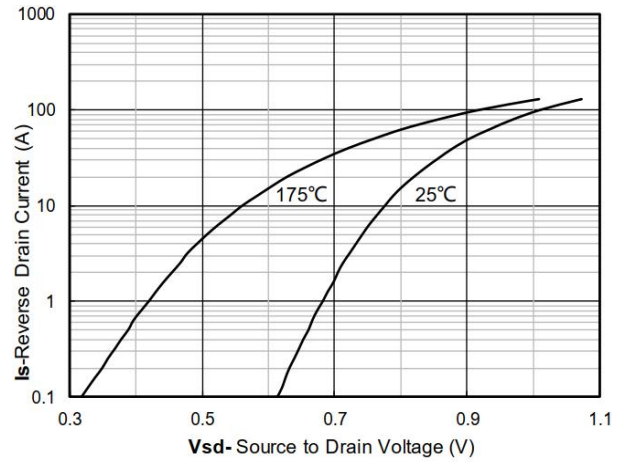


Figure 8. Forward characteristics of reverse diode

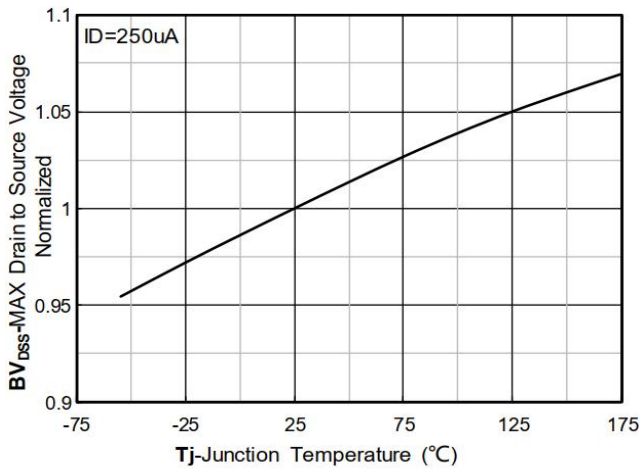


Figure 9. Normalized breakdown voltage

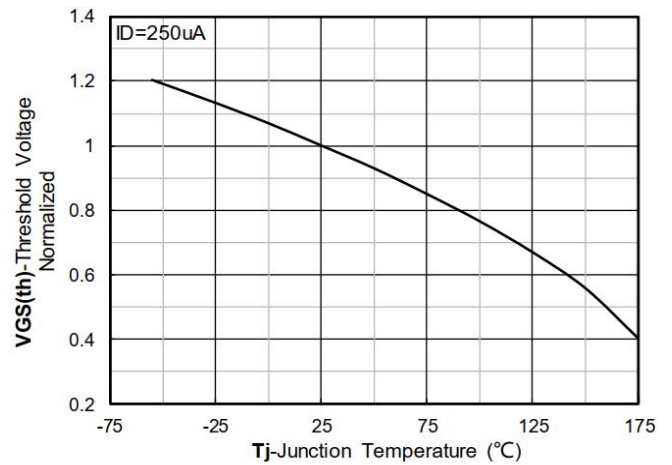


Figure 10. Normalized Threshold voltage

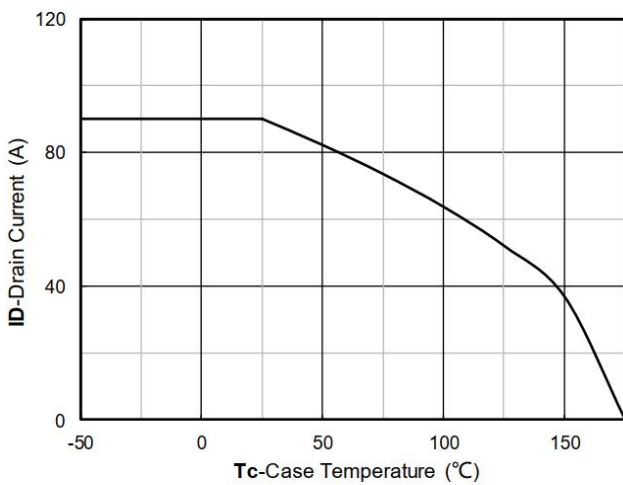


Figure 11. Current dissipation

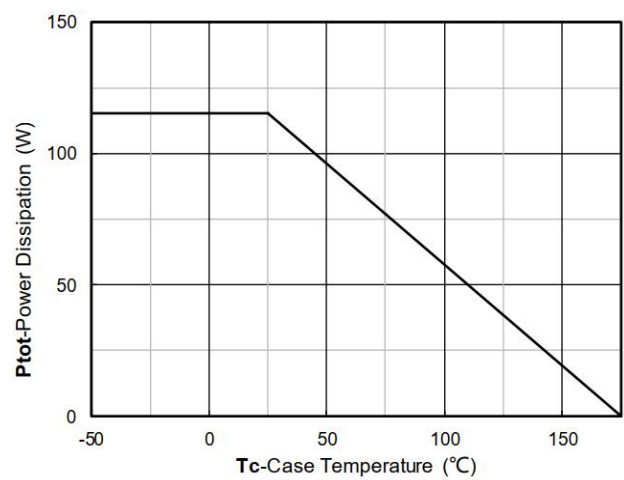


Figure 12. Power dissipation

Typical Characteristics

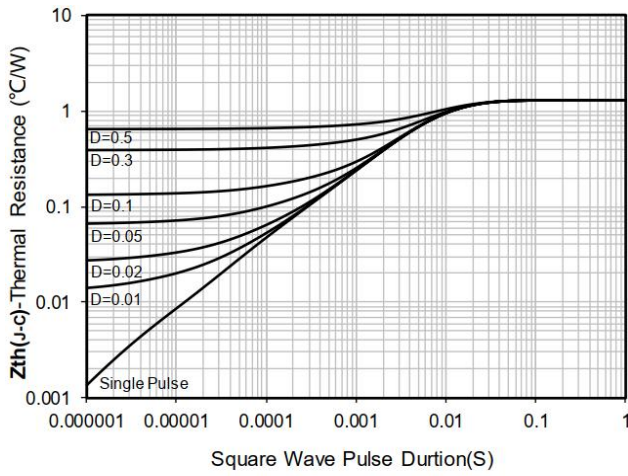


Figure 13. Maximum Transient Thermal Impedance

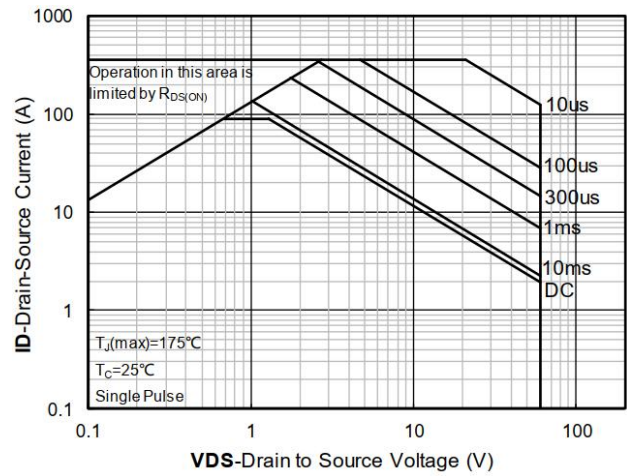
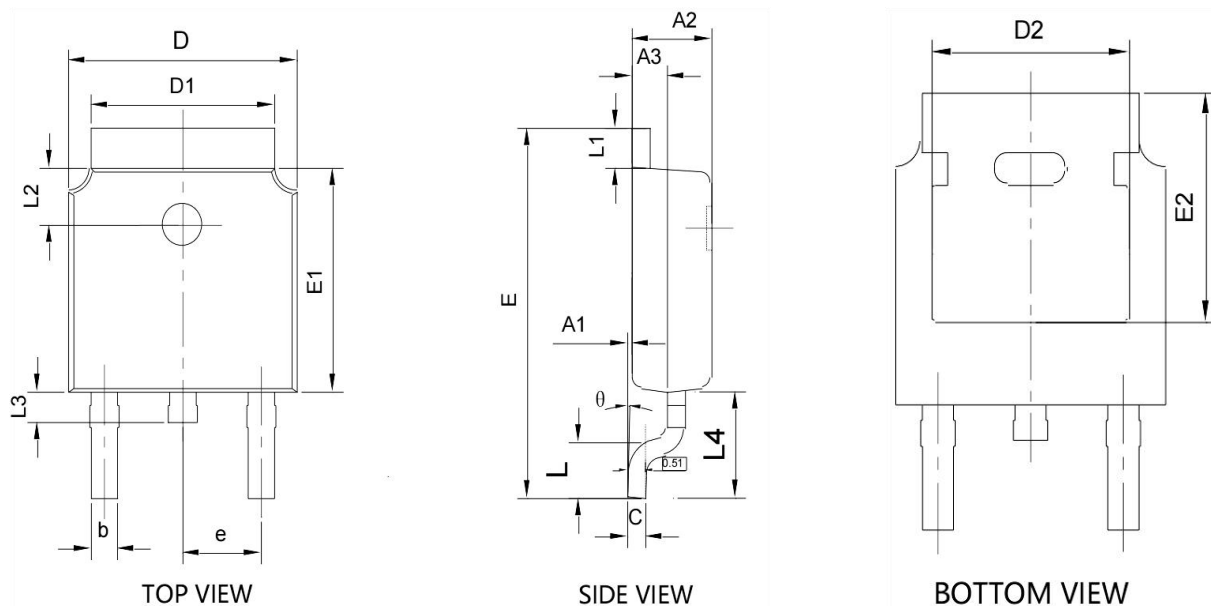


Figure 14. Safe Operation Area

TO-252AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A1	0.000	0.200	0.000	0.008
A2	2.200	2.400	0.087	0.094
A3	0.900	1.100	0.035	0.043
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.150	5.450	0.203	0.215
D2	4.600	4.950	0.181	0.195
E	9.900	10.300	0.390	0.406
E1	6.000	6.200	0.236	0.244
E2	5.150	5.450	0.203	0.215
e	2.286 BSC.		0.090 BSC.	
L	1.250	1.750	0.049	0.069
L1	0.900	1.270	0.035	0.050
L2	1.400	1.900	0.055	0.075
L3	0.600	1.000	0.024	0.039
L4	2.900 REF.		0.114 REF.	
θ	0°	10°	0°	10°